

## **isc Silicon PNP Power Transistor**

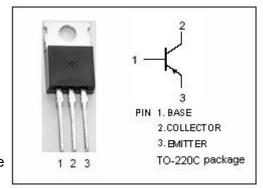
# **MJE5731**

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -350V(Min)
- DC current gain -
  - : h<sub>FE</sub> = 30~150@ I<sub>C</sub>= -0.3A
- With TO-220 Package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

 Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications

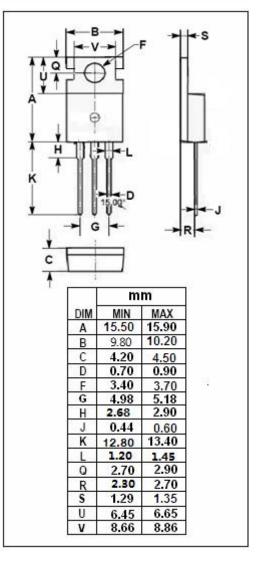


## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-350	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-350	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current-Continuous	-1	А
Ісм	Collector Current-Peak	-3	Α
I <sub>B</sub>	Base Current	-1	Α
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	2	
	Collector Power Dissipation @T <sub>C</sub> =25℃	40	W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~150	$^{\circ}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.125	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA ;I <sub>B</sub> = 0	-350		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A ;I <sub>B</sub> = -0.2A		-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -10V		-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -350V; I <sub>E</sub> = 0		-1.0	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -350V; I <sub>B</sub> = 0		-1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.3A; V <sub>CE</sub> = -10V	30	150	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -10V	10		
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = -0.2A;V <sub>CE</sub> = -10V; f <sub>test</sub> = 2.0MHz	10		MHz

Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2%.

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